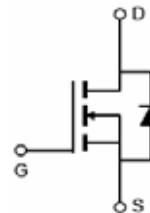


N-Channel Super Trench Power MOSFET

Description

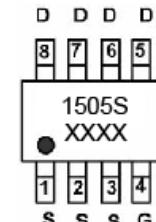
The RM1505S uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.



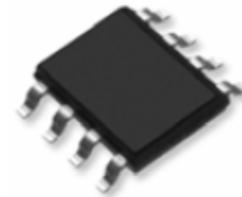
Schematic diagram

General Features

- $V_{DS} = 150V, I_D = 5.1A$
- $R_{DS(ON)} < 65m\Omega @ V_{GS}=10V$ (Typ: $55m\Omega$)
- Excellent gate charge $\times R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature



Marking and pin assignment



SOP-8 top view

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
1505S	RM1505S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current-Continuous		I_D	5.1	A
Drain Current-Continuous($T_C=100^\circ C$)		$I_D (100^\circ C)$	3.6	A
Pulsed Drain Current ^(Note 1)		I_{DM}	20	A
Single pulse avalanche energy ^(Note 5)		E_{AS}	60	mJ
Maximum Power Dissipation	$T_C = 25^\circ C$	P_D	5	W
	$T_A = 25^\circ C$		3	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	25	

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

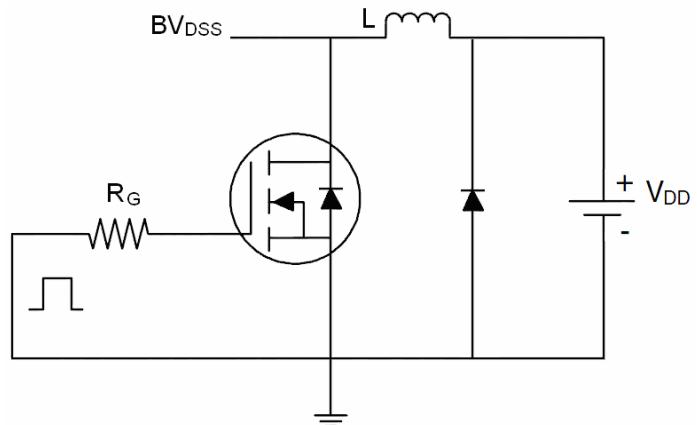
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=150\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.5	3.3	4.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=5.1\text{A}$	-	55	65	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=5.1\text{A}$	-	12.5	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{\text{DS}}=75\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	550	730	PF
Output Capacitance	C_{oss}		-	62	80	PF
Reverse Transfer Capacitance	C_{rss}		-	2.5	4.5	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=75\text{V}, I_{\text{D}}=5.1\text{A}$ $V_{\text{GS}}=10\text{V}, R_{\text{G}}=3\Omega$	-	7.5	14	nS
Turn-on Rise Time	t_r		-	1.4	8.5	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	12.5	21	nS
Turn-Off Fall Time	t_f		-	2.5	8	nS
Total Gate Charge	Q_g	$V_{\text{DS}}=75\text{V}, I_{\text{D}}=5.1\text{A}, V_{\text{GS}}=10\text{V}$	-	8.5	12	nC
Gate-Source Charge	Q_{gs}		-	2.8		nC
Gate-Drain Charge	Q_{gd}		-	1.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=5.1\text{A}$	-	-	1.2	V
Diode Forward Current (Note 2)	I_{S}		-	-	5.1	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = I_S$ $dI/dt = 100\text{A}/\mu\text{s}$ (Note 3)	-	58	95	nS
Reverse Recovery Charge	Q_{rr}		-	69	110	nC

Notes:

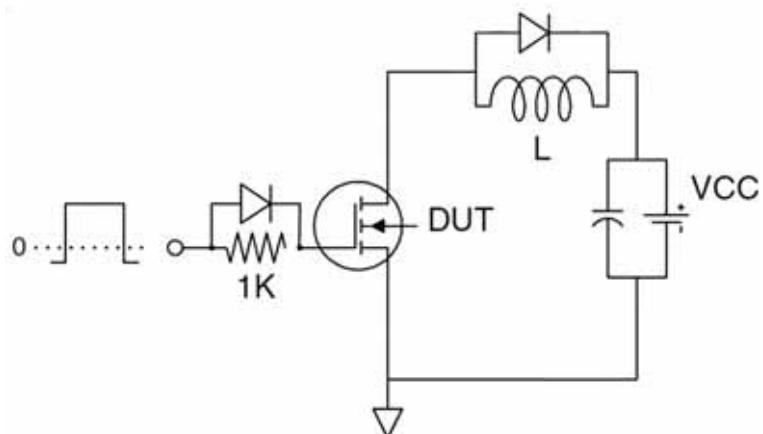
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- The value of R_{GJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design.
- Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- Guaranteed by design, not subject to production
- EAS condition : $T_J=25^\circ\text{C}, V_{\text{DD}}=50\text{V}, V_G=10\text{V}, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit

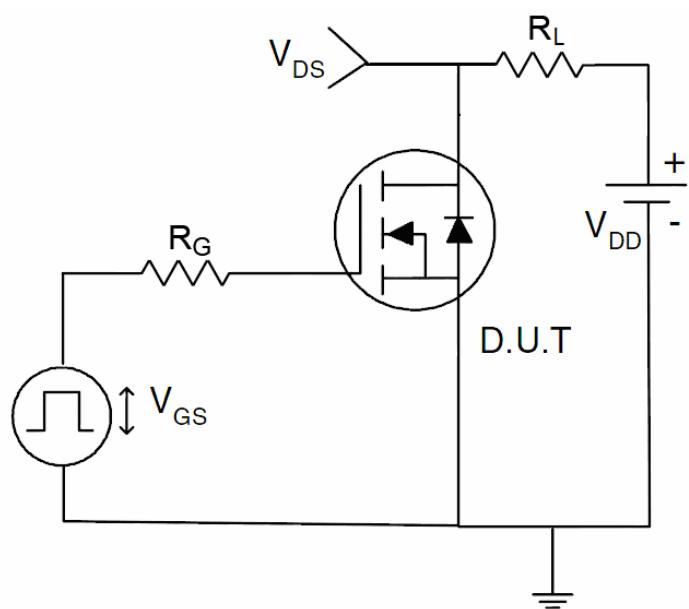
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM1505S)

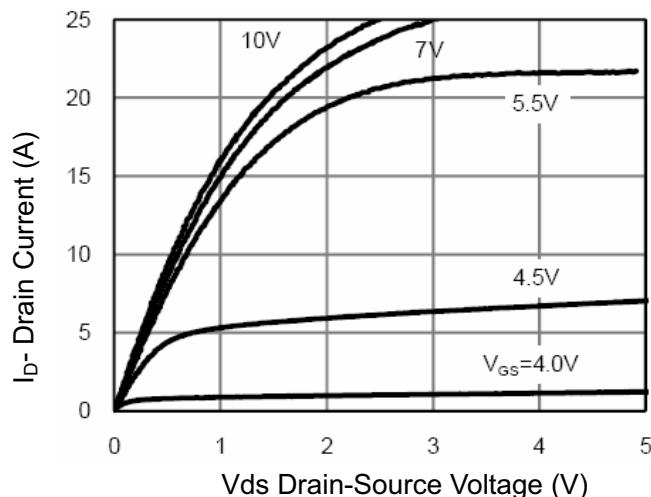


Figure 1 Output Characteristics

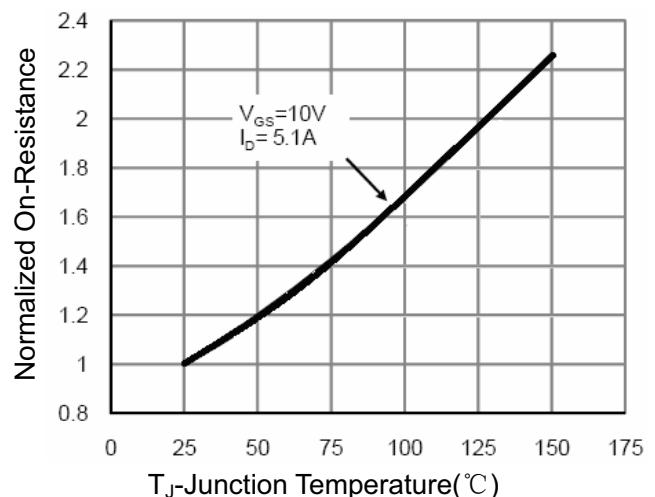


Figure 4 Rdson-JunctionTemperature

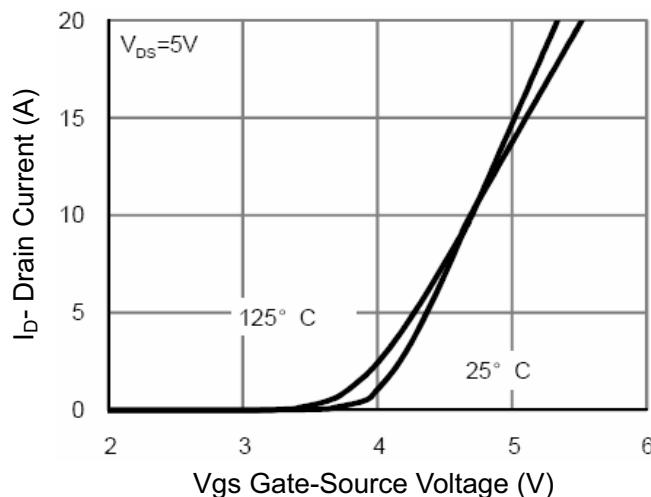


Figure 2 Transfer Characteristics

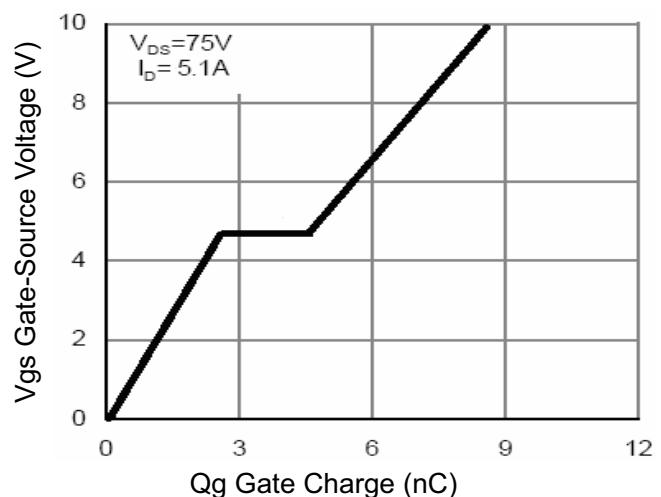


Figure 5 Gate Charge

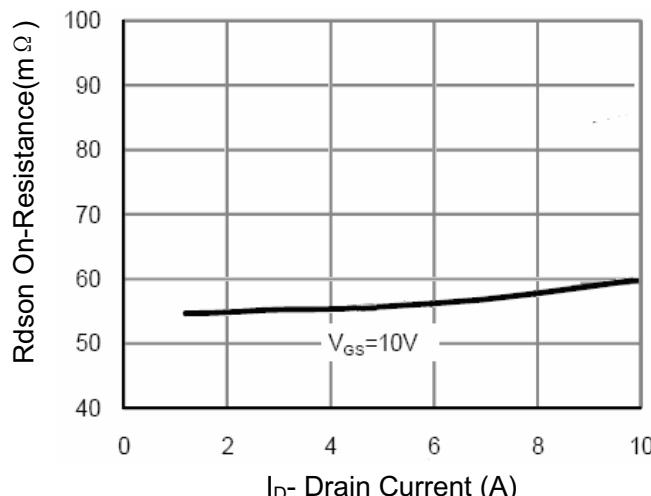


Figure 3 Rdson- Drain Current

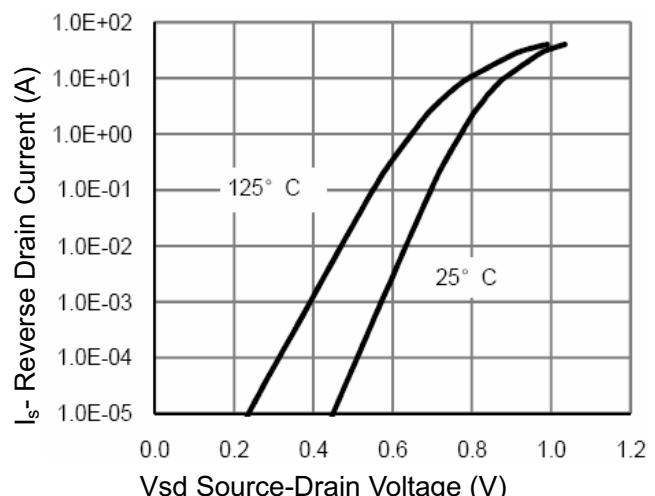


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM1505S)

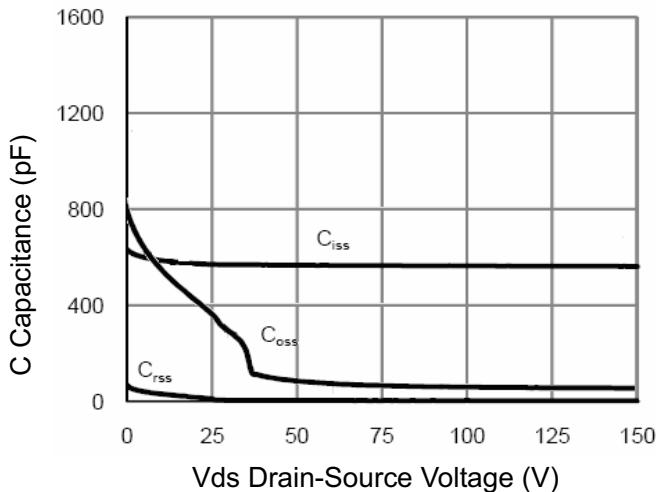


Figure 7 Capacitance vs Vds

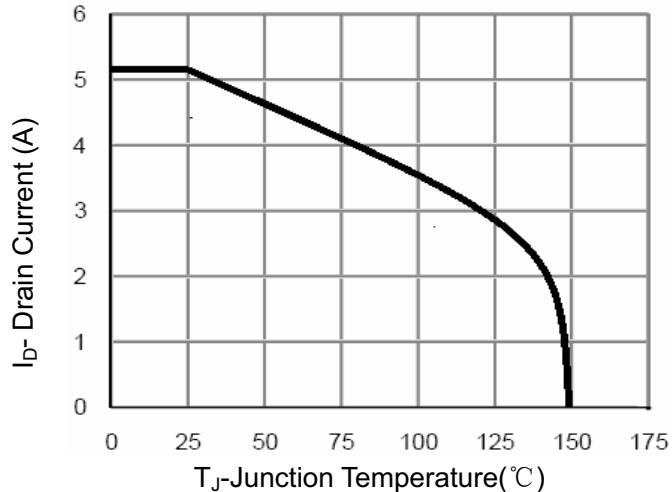


Figure 9 Current De-rating

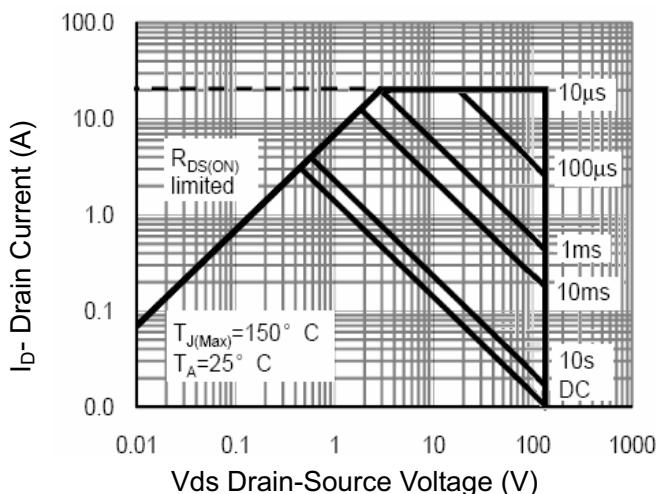


Figure 8 Safe Operation Area

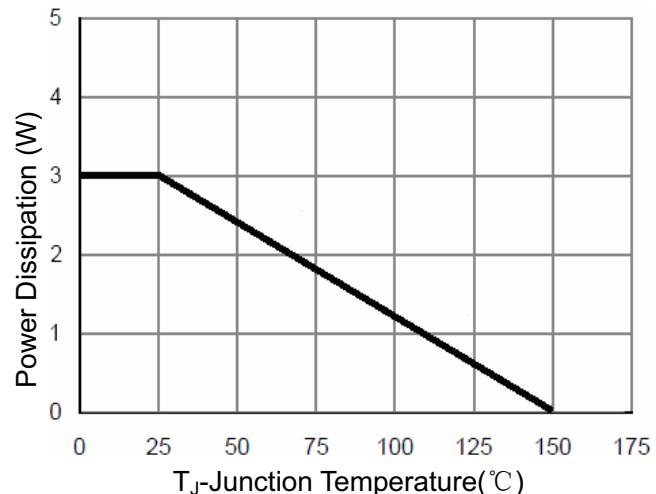


Figure 10 Power De-rating

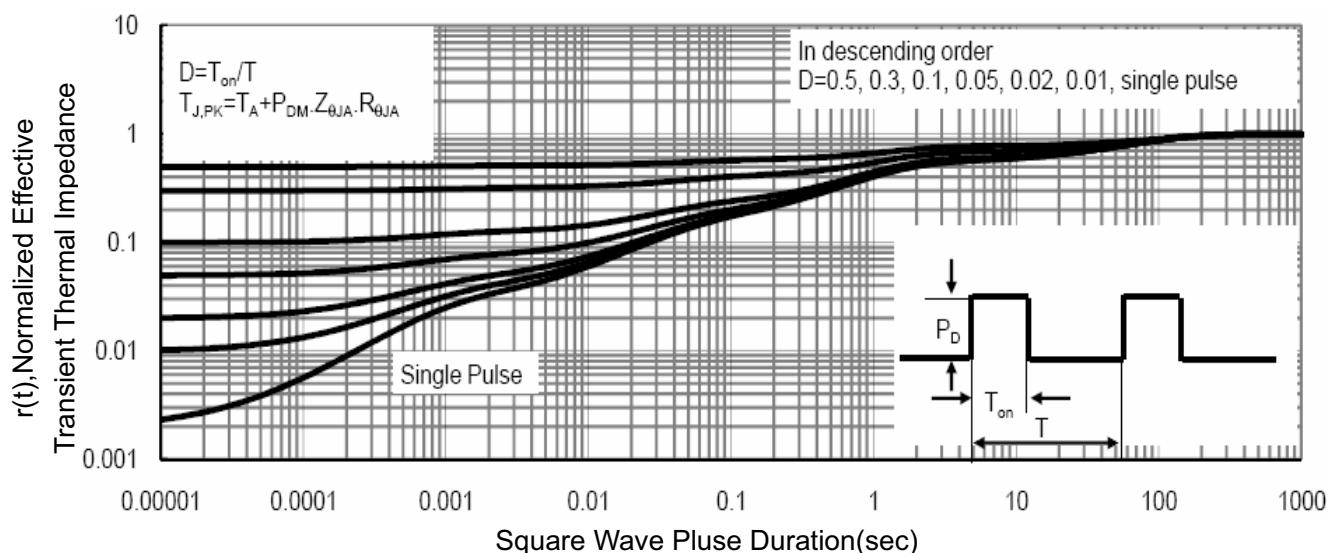
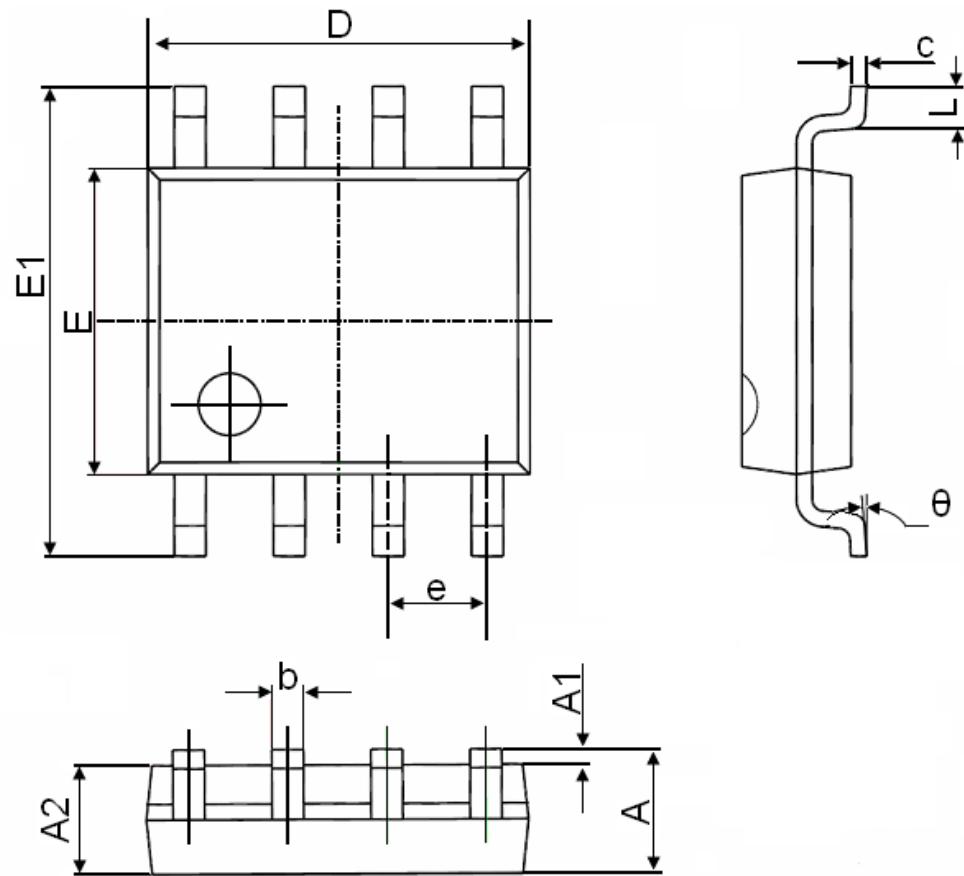


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Package	Tube (pcs/tube)	Tube (pcs/inner box)	Tube (pcs/cartoon)	Tape&Reel (pcs/reel)	Tape&Reel (pcs/inner box)	Tape&Reel (pcs/cartoon)
DFN5x6/DFN3x3	100	10,000	100,000	2,500	5,000	40,000
DFN1006	—	—	—	10,000	10,000	400,000
SOP-8	100	10,000	100,000	4,000	4,000	20,000
TSSOP-8	100	32,000	128,000	3,000	6,000	48,000
SOT-23-3L	—	—	—	3,000	30,000	120,000
SOT-23-6L	—	—	—	3,000	30,000	120,000
SOT-23(6R)	—	—	—	3,000	30,000	120,000
SOT-363	—	—	—	3,000	30,000	120,000
SOT-523	—	—	—	3,000	30,000	120,000
SOT223	—	—	—	2,500	2,500	20,000
TO-220	50	1,000	5,000	—	—	—
TO-220F	50	1,000	10,000	—	—	—
TO-247	30	300	1,200	—	—	—
TO-251	80	4,000	40,000	—	—	—
TO-251S(4R)	80	4,000	40,000	—	—	—
TO-252-2L(4R)	80	4,000	40,000	2,500	2,500	25,000
TO-263-2L	50	1,000	10,000	800	800	8,000
TO-3P	30	300	3,000	—	—	—
TO-92	—	—	—	1,000(袋装)	10,000	100,000

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